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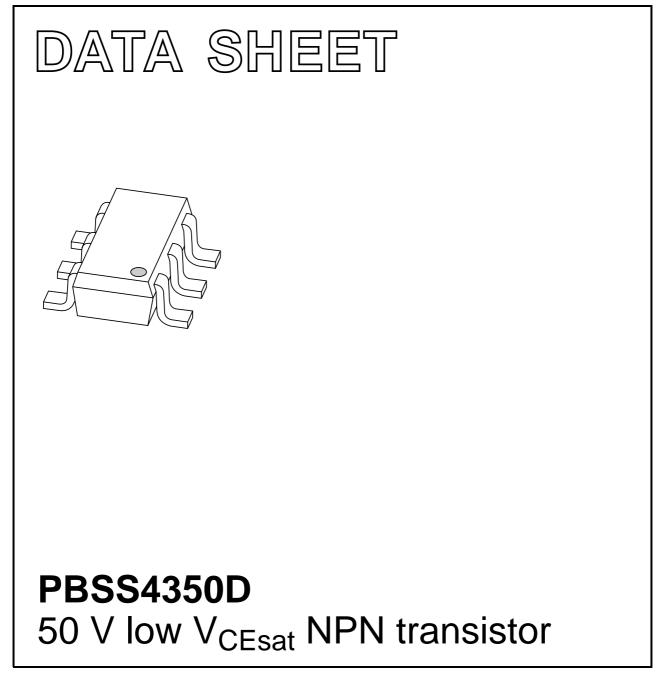
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2001 Jan 26 2001 Jul 13



PBSS4350D

50 V low V_{CEsat} NPN transistor

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Replacement for SOT89/SOT223 standard packaged transistors due to enhanced performance.

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC convertor applications
- · Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT457 (SC-74) plastic package. PNP complement: PBSS5350D.

MARKING

TYPE NUMBER	MARKING CODE		
PBSS4350D	43		

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT	
V _{CEO}	collector-emitter voltage	50	V	
I _{CM}	peak collector current	5	А	
R _{CEsat}	equivalent on-resistance	<145	mΩ	

PINNING

PIN	DESCRIPTION	
1	collector	
2	collector	
3	base	
4	emitter	
5	collector	
6	collector	

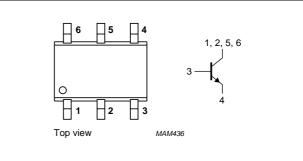


Fig.1 Simplified outline (SOT457; SC-74) and symbol.

PBSS4350D

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	50	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	3	A
I _{CM}	peak collector current		_	5	A
I _{BM}	peak base current		_	1	A
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$; note 1	_	600	mW
		$T_{amb} \le 25 \ ^{\circ}C$; note 2	_	750	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².
- 2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 6 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	208	K/W
ambient	in free air; note 2	160	K/W	

Notes

- 1. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².
- 2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 6 cm².

PBSS4350D

CHARACTERISTICS

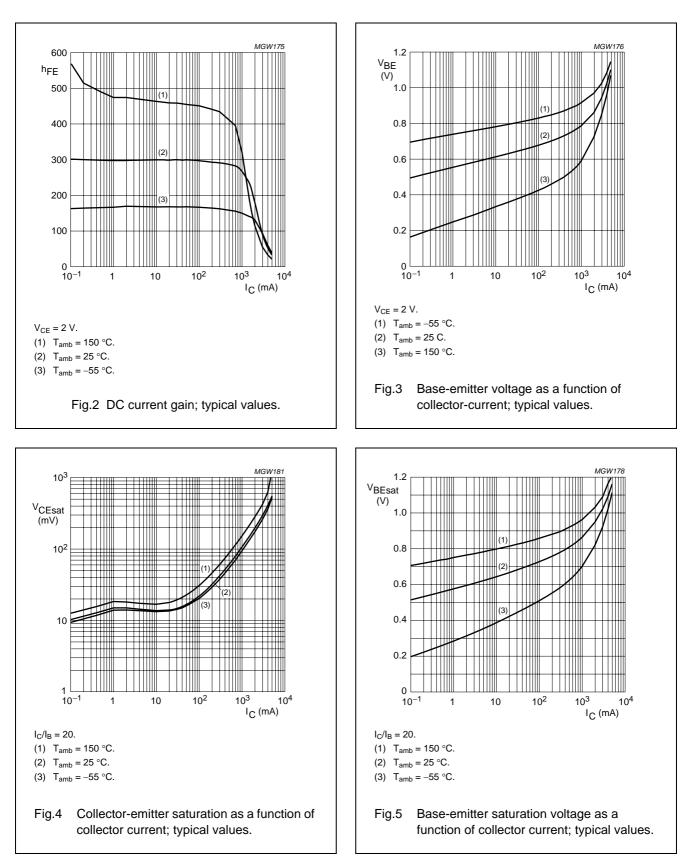
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{\text{E}} = 0$	-	-	100	nA
		V _{CB} = 50 V; I _E = 0; T _j = 150 °C	-	-	50	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0$	-	-	100	nA
h _{FE}	DC current gain	$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 500 \text{ mA}$	200	-	-	
		$V_{CE} = 2 V; I_{C} = 1 A; note 1$	200	-	-	
		$V_{CE} = 2 V; I_{C} = 2 A; note 1$	100	-	-	
V _{CEsat}	collector -emitter saturation	I _C = 500 mA; I _B = 50 mA	-	-	90	mV
	voltage	I _C = 1 A; I _B = 50 mA	-	-	170	mV
		I _C = 2 A; I _B = 200 mA; note 1	-	-	290	mV
R _{CEsat}	equivalent on-resistance	I _C = 2 A; I _B = 200 mA; note 1	-	110	<145	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 2 A; I _B = 200 mA; note 1	-	-	1.2	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 1 A; note 1	-	-	1.1	V
f _T	transition frequency	I_{C} = 100 mA; V_{CE} = 5 V; f = 100 MHz	100	_	_	MHz
Cc	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	_	_	30	pF

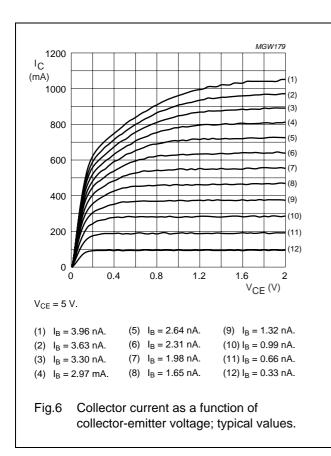
Note

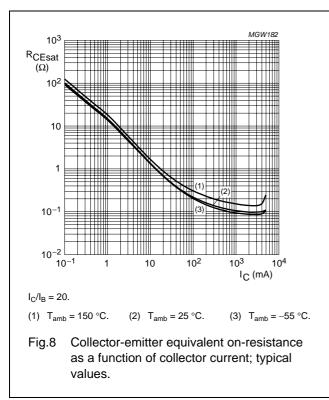
1. Pulse test: $t_p \leq 300~\mu\text{s};~\delta \leq 0.02.$

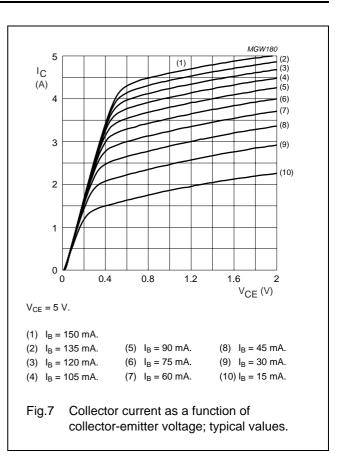
PBSS4350D



PBSS4350D







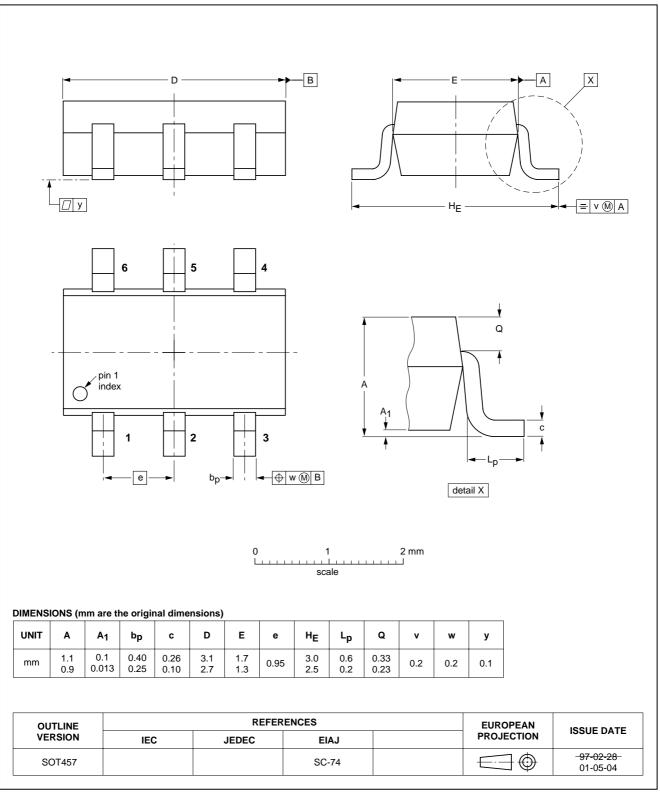
SOT457

PBSS4350D

50 V low V_{CEsat} NPN transistor

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads



PBSS4350D

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

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